

Contents

1. Introduction.....	1
1.1. Silicon-based thin-film solar cells.....	1
1.2. Outline.....	2
2. Doping in hydrogenated amorphous silicon.....	5
2.1. Substitutional doping in a-Si:H	5
2.2. Impurity distribution coefficients for arsenic and phosphorus	7
3. Experimental methods.....	11
3.1. Deposition of silicon films and solar cells.....	11
3.2. Material characterization.....	19
3.3. Solar cell characterization.....	26
4. Atmospheric contamination of a-Si:H films and solar cells	31
4.1. Introduction.....	31
4.2. Intentional impurity flows & impurity concentrations in the i-layer	33
4.3. Process conditions for the i-layer	35
4.4. Correlation of base pressure and impurity concentration.....	35
4.5. Solar cells based on contaminated i-layers	37
4.6. Material properties	40
4.7. Impact of local oxygen distribution in solar cells on critical base pressure	43
4.8. Light-induced degradation of contaminated solar cells	45
4.9. Discussion	48
4.10. Summary	52
5. Influence of the total process gas flow & deposition rate on impurity incorporation	53
5.1. Introduction.....	54
5.2. Process conditions of the i-layer	54
5.3. Correlation of base pressure and impurity concentration.....	55
5.4. Solar cells based on contaminated i-layers	57
5.5. Material properties	58
5.6. Light-induced degradation of solar cells.....	60
5.7. Discussion	63
5.8. Summary	67
6. Influence of impurity source on impurity incorporation.....	69

6.1.	Introduction.....	69
6.2.	Process conditions of the i-layer	70
6.3.	Material properties	70
6.4.	Amorphous solar cells based on contaminated i-layers.....	72
6.5.	Microcrystalline solar cells based on contaminated i-layers	74
6.6.	Correlation of base pressure and impurity concentration.....	75
6.7.	Light-induced degradation of solar cells.....	78
6.8.	Discussion.....	79
6.9.	Summary.....	82
7.	Impurity incorporation mechanisms	83
7.1.	Introduction.....	83
7.2.	Determination of distribution coefficient.....	84
7.3.	Nitrogen distribution coefficient	85
7.4.	Oxygen distribution coefficient	86
7.5.	Discussion.....	89
7.6.	Summary.....	94
8.	Single-chamber process.....	95
8.1.	Introduction.....	95
8.2.	Evaluation of reactor treatments (on a $10 \times 10 \text{ cm}^2$ scale)	97
8.3.	Single-chamber processes (on a $40 \times 40 \text{ cm}^2$ scale).....	100
8.4.	Discussion.....	113
8.5.	Summary.....	116
9.	Conclusion & outlook.....	119
9.1.	Atmospheric contamination of a-Si:H	119
9.2.	Atmospheric contamination of μc -Si:H.....	122
9.3.	Single-chamber process	122
9.4.	Outlook.....	123
10.	References	125
11.	Appendix.....	135
12.	Acknowledgements.....	137